

CLL4150

**SURFACE MOUNT
HIGH SPEED SILICON
SWITCHING DIODE**



SOD-80 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CLL4150 type is an ultra-high speed silicon switching diode manufactured by the epitaxial planar process, in a hermetically sealed glass surface mount package, designed for high speed switching applications.

MARKING: CATHODE BAND

MAXIMUM RATINGS: ($T_A=25^{\circ}\text{C}$)

Continuous Reverse Voltage
Peak Repetitive Reverse Voltage
Continuous Forward Current
Peak Repetitive Forward Current
Peak Forward Surge Current, $t_p=1.0\mu\text{s}$
Peak Forward Surge Current, $t_p=1.0\text{s}$
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V_R 50
 V_{RRM} 50
 I_F 300
 I_{FRM} 600
 I_{FSM} 4.0
 I_{FSM} 1.0
 P_D 500
 T_J, T_{stg} -65 to +200
 Θ_{JA} 350

UNITS

V
V
mA
mA
A
A
mW
 $^{\circ}\text{C}$
 $^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

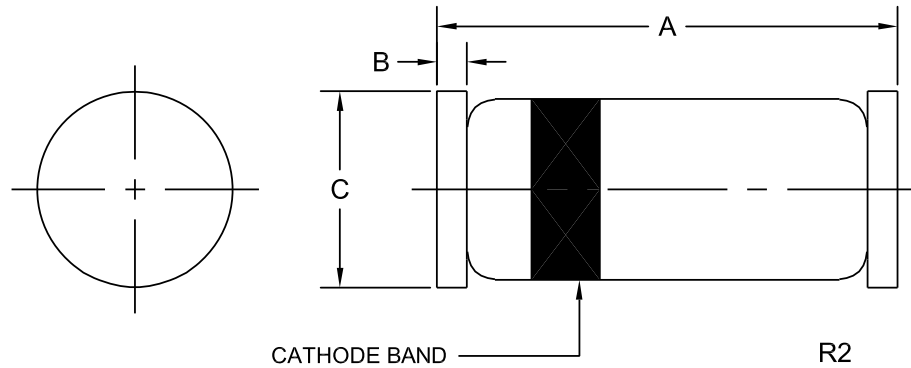
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	$V_R=50\text{V}$		100	nA
BV_R	$I_R=5.0\mu\text{A}$	75		V
V_F	$I_F=1.0\text{mA}$	0.54	0.62	V
V_F	$I_F=10\text{mA}$	0.66	0.74	V
V_F	$I_F=50\text{mA}$	0.76	0.86	V
V_F	$I_F=100\text{mA}$	0.82	0.92	V
V_F	$I_F=200\text{mA}$	0.87	1.0	V
C_T	$V_R=0$, $f=1.0\text{ MHz}$		4.0	pF
t_{rr}	$I_R=I_F=10\text{mA}$, $R_L=100\Omega$, Rec. to 1.0mA		4.0	ns

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SOD-80 CASE - MECHANICAL OUTLINE



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DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.130	0.146	3.30	3.71
B	0.014		0.35	
C (DIA)	0.049	0.067	1.25	1.70

SOD-80 (REV:R2)

R3 (8-January 2010)